

2RI 100G-120/160

POWER DIODE MODULE

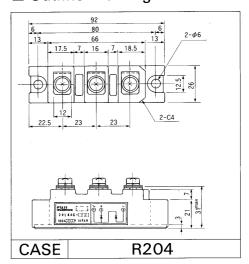
Features

- All the terminals and the mounting plate are electrically isolated. These modules can be installed in the same cooling fin as other modules, thus saving installation space –a cost-effective feature.
- The diode chips are coated with a glass of zinc oxide, making them highly resistant to temperature and humidity variation.
- Two diodes chips are connected in series internally, so allowing the rectifying circuit to be simplified.

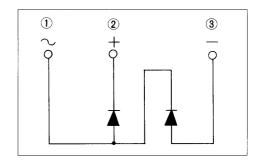
Applications

- Inverters for AC motors
- Power supply units for DC motors
- DC power supply units for battery chargers
- General purpose DC power supply units

■ Outline Drawings



■ Inner Circuit Schematic



■ Maximum Ratings and Characteristics

Absolute Maximum Ratings

ltems	Symbols	Conditions	2RI100G		Units
			-120	-160	Units
Repetitive peak reverse voltage	V _{RRM}		1200	1600	V
Non-repetitive peak reverse voltage	V _{RSM}		1320	1760	V
Average forward current	I _{F(AV)}	50/60 Hz Sinewave.T _C = 98°C	2×100		А
Surge current	I _{FSM}	Rated load conditions, 10 ms	1200		Α
	l ² t	Rated load conditions	16000		A ² s
Junction temperature	T _i		-40~+150		°C
Storage temperature	T _{stg}		-40~+125		°C
Tightening torque		Mounting screw: M5	25±5		kg⋅cm
Vibration resistance			5		G
Dielectric strength		Between terminals and base	2500 VAC 1min		
Net. Weight			180		g

• Electrical Characteristics

Items	Symbols	Conditions	Min	Тур	Max	Units
Forward voltage	V_{FM}	$T_j = 25$ °C, $I_{FM} = 320 \text{ A}$			1.40	V
Reverse current	I _{RRM}	$T_j=150$ °C, $V_R=V_{RRM}$			30	mA

Thermal Characteristics

Items	Symbols	Conditions	Min	Тур	Max	Units
Thermal resistance (Junction to case)	R _{th(j-c)}	50/60 Hz Sinewave, Thermal resistance for total loss			0.20	°C/W
Thermal resistance	R _{th(c-f)}	With thermal compound			0.10	°C/W